

BAS40-06LT1

Preferred Device

Common Anode Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage
- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	40	V

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_F	225 1.8	mW mW/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Forward Continuous Current	I_{FM}	120	mA
Single Forward Current $t \leq 1 \text{ s}$ $t \leq 10 \text{ ms}$	I_{FSM}	200 600	mA
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	508 (Note 1) 311 (Note 2)	$^\circ\text{C}/\text{W}$

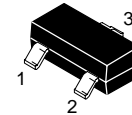
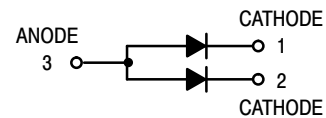
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ minimum pad.
2. FR-4 @ 1.0 x 1.0 in pad.



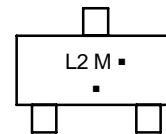
ON Semiconductor®

40 VOLTS SCHOTTKY BARRIER DIODE



SOT-23 (TO-236AB)
CASE 318
STYLE 12

MARKING DIAGRAM



L2 = Specific Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAS40-06LT1	SOT-23	3000/Tape & Reel
BAS40-06LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

BAS40-06LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	40	-	V
Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	-	5.0	pF
Reverse Leakage ($V_R = 25 \text{ V}$)	I_R	-	1.0	μA_{dc}
Forward Voltage ($I_F = 1.0 \text{ mAdc}$)	V_F	-	380	mVdc
Forward Voltage ($I_F = 10 \text{ mAdc}$)	V_F	-	500	mVdc
Forward Voltage ($I_F = 40 \text{ mAdc}$)	V_F	-	1.0	Vdc

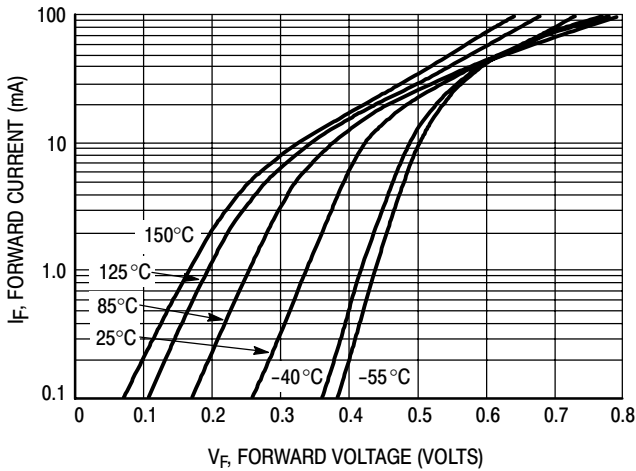


Figure 1. Typical Forward Voltage

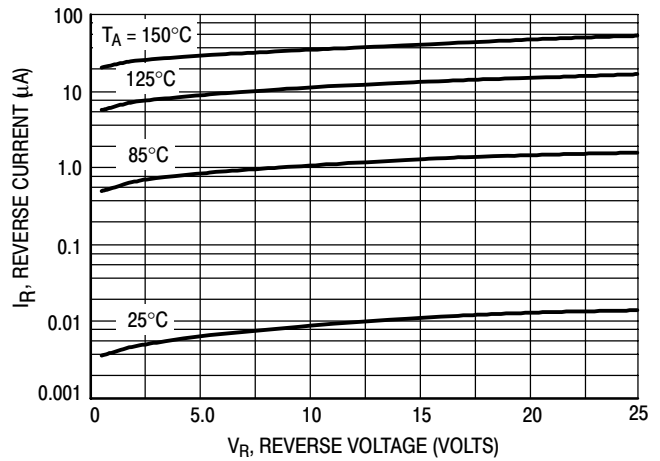


Figure 2. Reverse Current versus Reverse Voltage

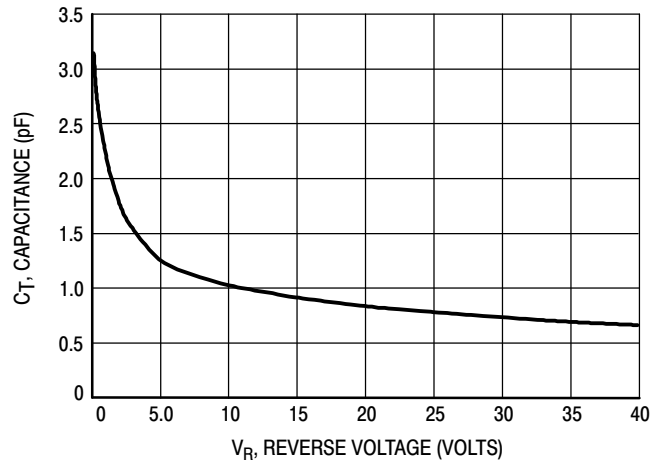
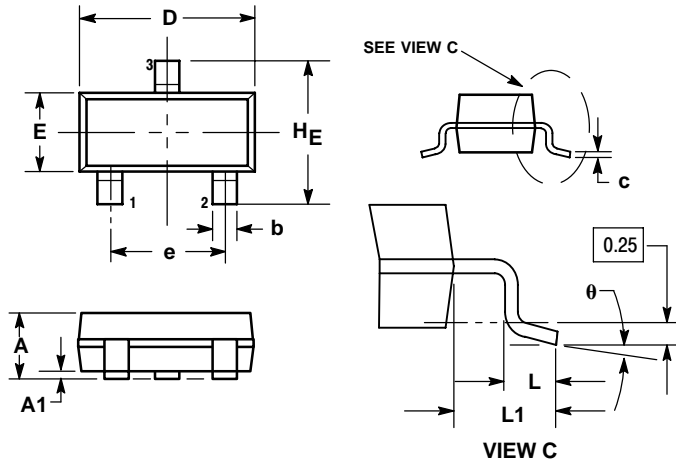


Figure 3. Typical Capacitance

BAS40-06LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

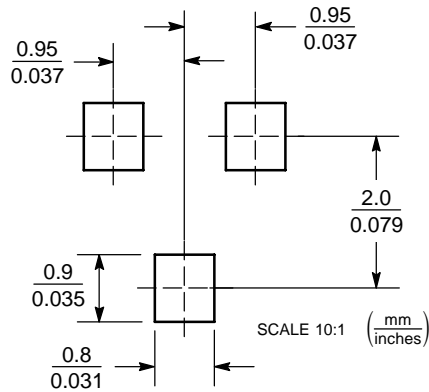
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 12:

- PIN 1. CATHODE
2. CATHODE
3. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.